



- Find the solution of the equation $3x(xy - 2)dx + (x^3 + 2y)dy = 0$. (10 分)
- Find the solution of the equation $y'' - 2y' - 3y = 3t^2 + 4t - 5$ with $y(0) = 9$ and $y'(0) = -4$. (15 分)
- Find the solution of the system $\begin{cases} x_1' = 5x_1 - 3x_2 + 8 \\ x_2' = x_1 + x_2 + 32t \end{cases}$ with $\begin{cases} x_1(0) = 2 \\ x_2(0) = 0 \end{cases}$. (15 分)
- Find the solution of the equation $y'' - 3y' + 2y = 4e^{2t}$ with $y(0) = -3$ and $y'(0) = 5$. (10 分)

(a) Prove that the Laplace transform of $4e^{2t}$ is $\frac{4}{s-2}$.

(b) Solving the differential equation by using Laplace transform.

- Perform the indicated operation, give that (10 分)

$$A = \begin{bmatrix} 1 & 0 & -2 \\ 2 & 2 & 3 \end{bmatrix} \quad B = \begin{bmatrix} 2 & 3 & 0 \\ 0 & -2 & 4 \end{bmatrix} \quad C = \begin{bmatrix} 1 & 2 \\ 4 & 3 \\ 0 & -1 \end{bmatrix}$$

(a) $(A+B)C$ (b) If $2X - 6(2A - B) = 0$, Find X.

- Find the eigenvalues and eigenvectors of A. (10 分)

$$A = \begin{bmatrix} 2 & 0 & 1 \\ 0 & 1 & 0 \\ 2 & 0 & 3 \end{bmatrix}$$

- (a) A real square matrix $A = [a_{jk}]$. Define the following terms: (using by A^T , A , A^{-1})
 (1) Symmetric matrix (2) Skew-Symmetric matrix (3) Orthogonal matrix (6 分)

(b) Determine the nature (Symmetric or Skew-Symmetric or Orthogonal) of the following matrices. (8 分)

$$A = \begin{bmatrix} 1 & 2 \\ 2 & 3 \end{bmatrix}, \quad B = \begin{bmatrix} \frac{\sqrt{3}}{2} & \frac{-1}{2} \\ \frac{1}{2} & \frac{\sqrt{3}}{2} \end{bmatrix}, \quad C = \begin{bmatrix} 0 & 9 & -12 \\ -9 & 0 & 20 \\ 12 & -20 & 0 \end{bmatrix}, \quad D = \begin{bmatrix} 1/7 & 3/7 & 2/7 \\ 3/7 & 2/7 & 5/7 \\ 2/7 & 5/7 & 3/7 \end{bmatrix}$$

- If $\vec{A} = 2\vec{i} + \vec{j} - \vec{k}$, $\vec{B} = \vec{i} - 3\vec{j} - 5\vec{k}$ Find (a) $\vec{A} \cdot \vec{B}$ (b) $\vec{A} \times \vec{B}$ (c) the $\cos\theta$ between \vec{A} and \vec{B} (d) the projection of \vec{A} on \vec{B} . (16 分)



1. Explain the following terms
 - (a) Heterojunction (5%)
 - (b) Fixed Oxide charge (5%)
 - (c) Schottky barrier potential of a metal/p-type junction (5%)
 - (d) Threshold voltage (5%)

2. For a pin junction, the charge distribution is shown in Fig.1. Draw the field and voltage distributions and find the applied voltage. (15%)
 ($n_i=10^{10}/\text{cm}^3$, $kT=0.025\text{eV}$, $\ln 10=2.3$)

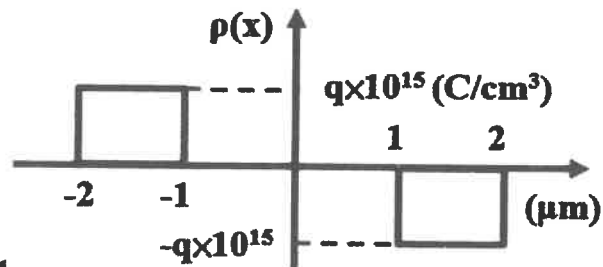


Fig.1

3. Describe the reasons the dominate current is electron or hole current of (a) p^+n and (b) p^+N junctions, where + and N mean high doping concentration and wider band gap, respectively. (15%)

4. Explain or define the following terms:
 - (a) N-type dopants for Silicon (5%)
 - (b) Depletion region of p-n junction (5%)
 - (c) Hole carriers in a semiconductor (5%)
 - (d) Electron mobility (5%)

5. Describe the advantages of direct bandgap for semiconductors. (15%)

6. Describe briefly the formation of the build-in potential in a p-n junction diode. (15%)



1. Convert the following 2's complement binary numbers to decimal. (20%)

- (a) 1010
- (b) 0110
- (c) 01011010
- (d) 11111110
- (e) 0011100111010011

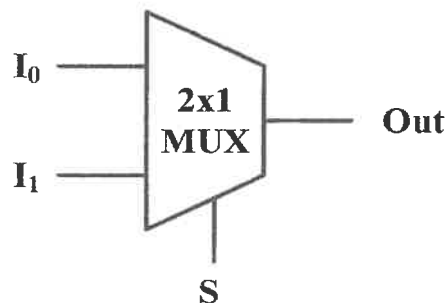
2. Implement the XOR function by means of : (10%)

- (a) NAND gates only.
- (b) NOR gates only.

Please draw the gate-level circuit.

3. Implement a 4-to-1 mux using only 2-to-1 muxes making sure to properly connect all of the terminals. Remember that you will have 4 inputs, 2 control signals, and 1 output. Write out the truth table for this circuit. (10%)

4. A symbol of 2-to-1 mux is listed below. Please draw the gate-level circuit of 2-to-1 mux. (10%)



5. Given an array of 100 elements. Write an algorithm or C program with comments to do bubble sort. Draw a flowchart. How many comparisons and how many swaps the algorithm will take at worst? What is the time complexity of this algorithm? Which sorting algorithm is faster than bubble sort? (13%)

6. Describe a Turing machine. What are the similarities between a Turing machine and a personal computer? What are the differences? (13%)



7. Write an algorithm to find all the prime numbers less than or equal to n . Use comments to explain your program and draw a flowchart to illustrate the algorithm. Show that your algorithm work for $n=25$ (12%)
8. Write down the Euclidean algorithm to find the greatest common divisor between two positive integers a and b . You cannot use any division or mod function but you can use subtraction. Write down a recursive version of the Euclidean algorithm. This recursive version can use the mod function. Show that both algorithms work with two examples for each algorithm? (12%)



本試題共五題，每題得分如各題中所示，共計 100 分，請依題號作答並將答案寫在答案卷上，違者不予計分。

- From the Voltage Transfer Characteristic (VTC), we can find four parameters of the VTC (V_{OH} , V_{OL} , V_{IL} , and V_{IH}). Determine the noise margins:
 - (5 分) NM_H and
 - (5 分) NM_L

- For the instrumentation amplifier of Fig. P2:

- (10 分) find the voltage v_1 and v_2 .
- (10 分) find the voltage v_3 and v_4 .
- (5 分) find the voltage v_o .

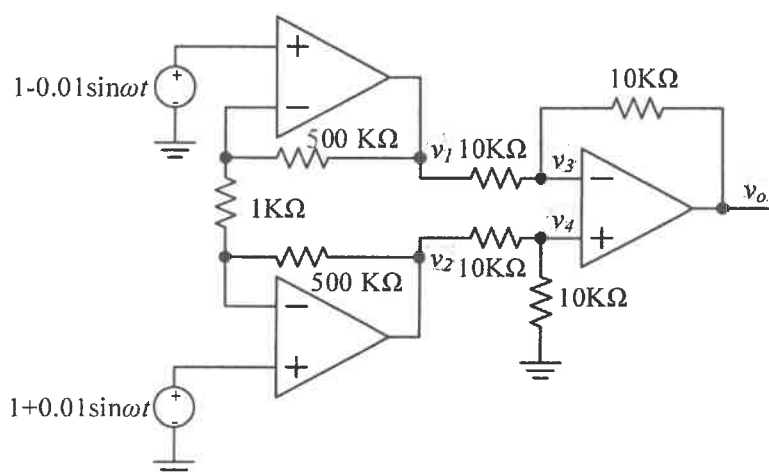


Fig. P2

- Assume the forward voltage of the diode which shown in Fig. 3(a)(b)and(c) is 0.1V with no leakage current.

- (5 分) Find the values of I_1 and V_1 in the circuits shown in Fig. P3(a).
- (5 分) Find the values of I_2 and V_2 in the circuits shown in Fig. P3(b).
- (5 分) Find the values of I_3 and V_3 in the circuits shown in Fig. P3(c).

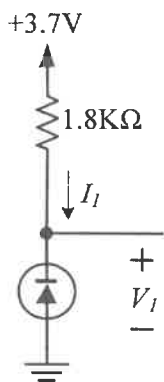


Fig. P3(a)

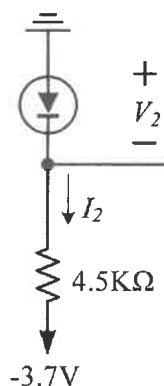


Fig. P3(b)

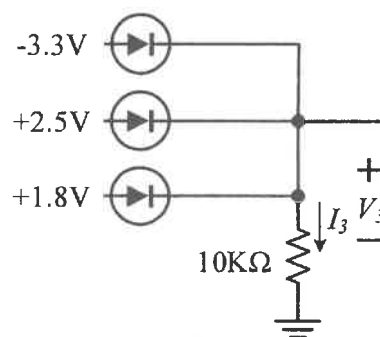


Fig. P3(c)



4. (20 分) The operational amplifiers are ideal. Please (a) calculate the voltage gains of the circuits shown in Fig. P4(a), where $R_1=10k\Omega$ and $R_2=100\Omega$. (b) Write down V_{out} in terms of $V_A, V_B, R_A, R_B,$ and $R_C,$ as shown in Fig. P4(b).

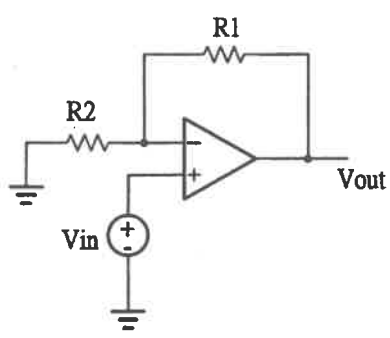


Fig. P4(a)

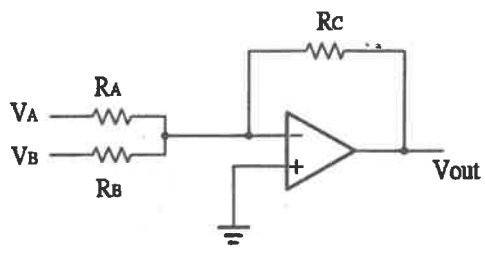


Fig. P4(b)

5. (30 分) All MOS transistors are biased in the saturation region. Neglect the body-effect of the NMOS transistors. Calculate (a) open-loop gain, (b) loop gain, and (c) closed-loop gain of the feedback amplifier shown in Fig. P5. $\lambda_N = \lambda_P = 0.1V^{-1}$. $g_{mN} = 10 \times 10^{-3} A/V$. $g_{mP} = 2.5 \times 10^{-3} A/V$. $I_{SS} = 2mA$. $R_1=100k\Omega$. $R_2=100k\Omega$.

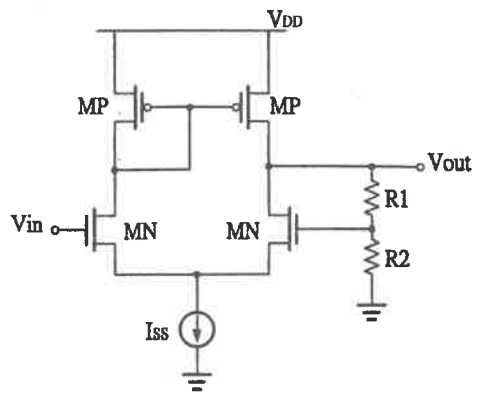


Fig. P5



Useful physical constants: $\epsilon_0 \approx \frac{10^{-9}}{36\pi}$ (F/m); $\mu_0 = 4\pi \times 10^{-7}$ (H/m)

- 請分別用微分與積分形式寫出基本電磁學的 4 個馬克斯威爾方程式，並解釋每個方程式的物理涵義。(12%)
- 有一電位 $V = 3x^2yz$ (V), x, y, z 代表笛卡兒座標。請寫出電場 \mathbf{E} 的方程式，並計算在座標 (3 m, 2m, 1m) 處的電場。(10%)
- 在原點有一個 20.0-nC 的點電荷。
 - 在真空的環境下，請計算離原點 1.0 m 處，電場 \mathbf{E} 與電通量密度 \mathbf{D} 。
 - 若此電荷是埋沒在很大體積的純水環境($\epsilon_r = 81$)中，請計算離原點 1.0 m 處，電場 \mathbf{E} 與電通量密度 \mathbf{D} 。
(使用球座標) (20%)
- 有一平板電容，在結構上兩個平行電極板間的介電質是可以移除的。若此平板電容在平行電極板間沒有任何介電質時，電容值是 8 nF；填充某介電質材料後，電容值變為 32 nF。求此介電材料的介電常數(dielectric constant/relative permittivity)是多少？(8%)
- 一電磁波的頻率為 10^8 Hz，波長為 2 m，
 - 求此電磁波的傳遞速度。
 - 若此電磁波的函數為 $A_0 \cos(\omega t - \beta z)$ ，求 ω 和 β 的值。
(20%)
- 請說明：
 - 磁場的單位。
 - 磁通量密度的單位。
 - 磁場和磁通量密度的關係。
(12%)
- 若 z 軸上有一無限長之導線，通有電流 I (往 $+z$ 方向)，
 - 請說明 y 軸上的 $(0, r, 0)$ 位置其磁場方向。
 - 請說明 $(0, r, 0)$ 位置其磁場大小與 r 的關係。
(18%)

